

Photoelectromagnetic detectors PEM

PEM series features room temperature IR detectors operate on the on the photoelectromagnetic effect in the semiconductors.

Detector type	Cooling, operating temperature $T [K]$	Optimal wavelength ^{*)} $\lambda_{opt} [\mu m]$	Detectivity ^{**)} $D^* \left[\frac{cm \cdot \sqrt{Hz}}{W} \right]$		Current responsivity length product $@\lambda_{opt}$ $R_s \cdot L_s \left[\frac{A \cdot mm}{W} \right]$	Time constant $\tau [ns]$	Resistance $R [\Omega]$	Acceptance angle $\varnothing \left[^\circ \right]_{-2\theta/4}$	Optical area ^{***)} $[mm \times mm]$	Package	Window ^{****)}
			@ λ_{peak}	@ λ_{opt}							
PEM	uncooled, ~300	10.6	$\geq 1.6 \times 10^7$	$\geq 1.0 \times 10^7$	≥ 0.002	≤ 1.2	40 to 100	~48, 1.23	1 x 1 2 x 2	PEM-SMA, PEM-TO8	wedged ZnSe AR coated

^{*)} Other optimal wavelengths available upon request.

^{**) Data sheet states minimum guaranteed D^* values for each detector model. Higher performance detectors can be provided upon request.}

^{***)} Other optical area available upon request.

^{****)} Other windows available upon request.

Photoelectromagnetic detectors optically immersed PEMI

PEMI series features room temperature IR detectors operate on the on the photoelectromagnetic effect in the semiconductor, optically immersed (achieved by using high refractive index micro lenses) in order to improve performance of the devices, different acceptance angle and saturation level. Both PEM/PEMI devices are typically optimized for the best performance at 10.6 μm . The detectors include active element based on HgCdTe band gap engineered with selected composition and doping profiles, and miniature permanent magnets to produce a magnetic field. Exhibiting no flicker noise, they can be at the same time used for detection of CW and low frequency modulated radiation in the whole 2 to 11 μm spectral range.

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			@ λ_{peak}	@ λ_{opt}							
PEMI	uncooled, ~300	10.6	$\geq 1.6 \times 10^8$	$\geq 1.0 \times 10^8$	≥ 0.01	≤ 1.2	40 to 100	~36, 1.62	1 x 1 2 x 2	PEM-SMA, PEM-TO8	wedged ZnSe AR coated

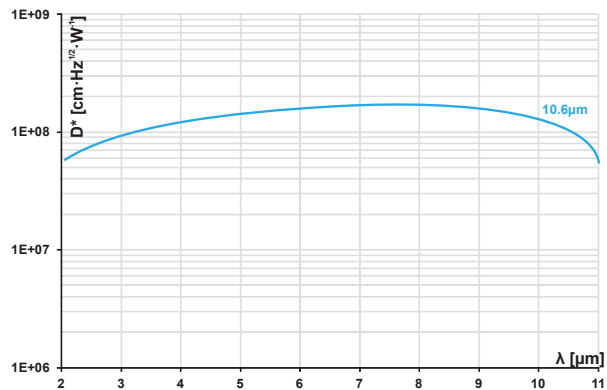
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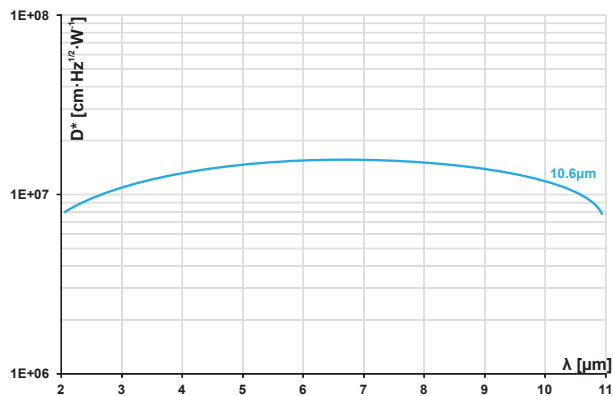


Spectral characteristics^{*)}

PEMI



PEM



^{*)}Example of D^* vs wavelength λ for HgCdTe detectors.
Spectral characteristics of individual detectors may vary from those shown on the chart.